



M29F100T M29F100B

1 Mbit (128Kb x8 or 64Kb x16, Boot Block) Single Supply Flash Memory

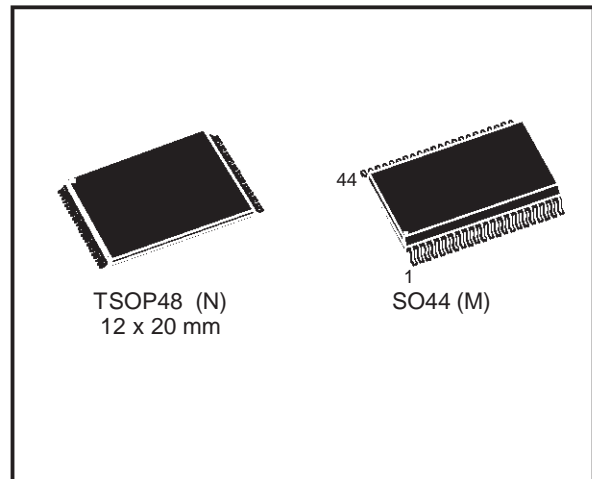
DATA BRIEFING

- 5V \pm 10% SUPPLY VOLTAGE for PROGRAM, ERASE and READ OPERATIONS
- FAST ACCESS TIME: 70ns
- FAST PROGRAMMING TIME
 - 10 μ s by Byte / 16 μ s by Word typical
- PROGRAM/ERASE CONTROLLER (P/E.C.)
 - Program Byte-by-Byte or Word-by-Word
 - Status Register bits and Ready/Busy Output
- MEMORY BLOCKS
 - Boot Block (Top or Bottom location)
 - Parameter and Main blocks
- BLOCK, MULTI-BLOCK and CHIP ERASE
- MULTI-BLOCK PROTECTION/TEMPORARY UNPROTECTION MODES
- ERASE SUSPEND and RESUME MODES
 - Read and Program another Block during Erase Suspend
- LOW POWER CONSUMPTION
 - Stand-by and Automatic Stand-by
- 100,000 PROGRAM/ERASE CYCLES per BLOCK
- 20 YEARS DATA RETENTION
 - Defectivity below 1ppm/year
- ELECTRONIC SIGNATURE
 - Manufacturer Code: 0020h
 - Device Code, M29F100T: 00D0h
 - Device Code, M29F100B: 00D1h

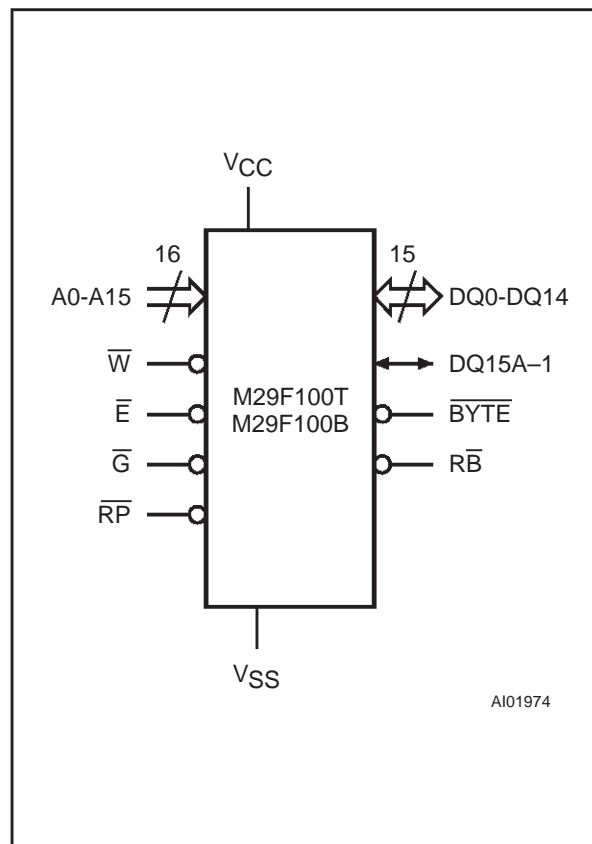
DESCRIPTION

The M29F100 is a non-volatile memory that may be erased electrically at the block or chip level and programmed in-system on a Byte-by-Byte or Word-by-Word basis using only a single 5V V_{CC} supply. For Program and Erase operations the necessary high voltages are generated internally. The device can also be programmed in standard programmers.

The array matrix organisation allows each block to be erased and reprogrammed without affecting other blocks. Blocks can be protected against programming and erase on programming equipment, and temporarily unprotected to make changes in the application. Each block can be programmed and erased over 100,000 cycles.

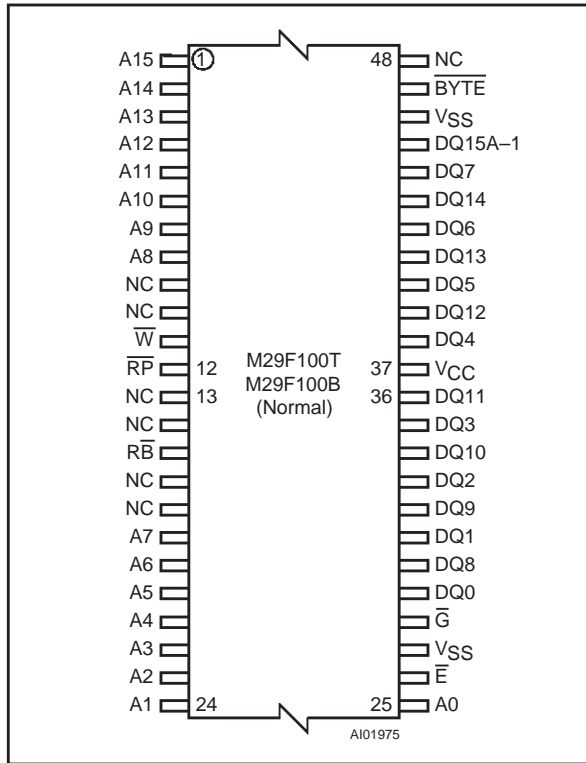


Logic Diagram



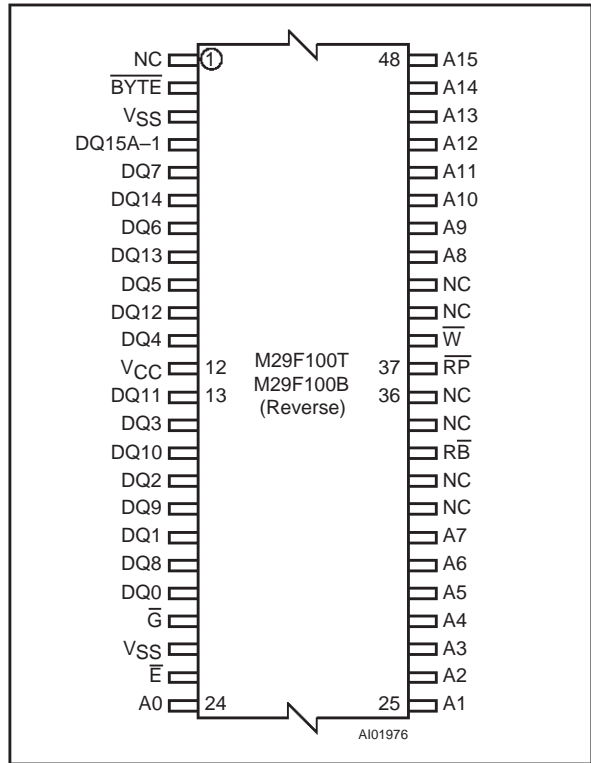
M29F100T, M29F100B

TSOP Pin Connections



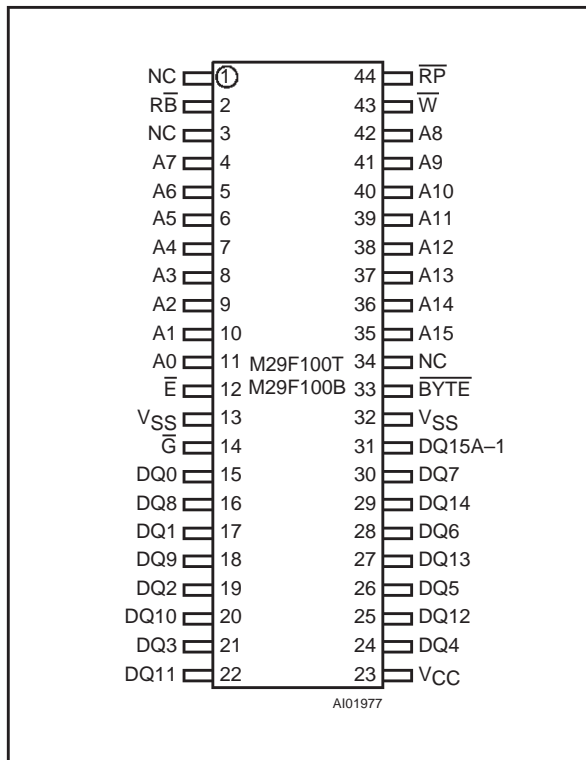
Warning: NC = Not Connected.

TSOP Reverse Pin Connections



Warning: NC = Not Connected.

SO Pin Connections

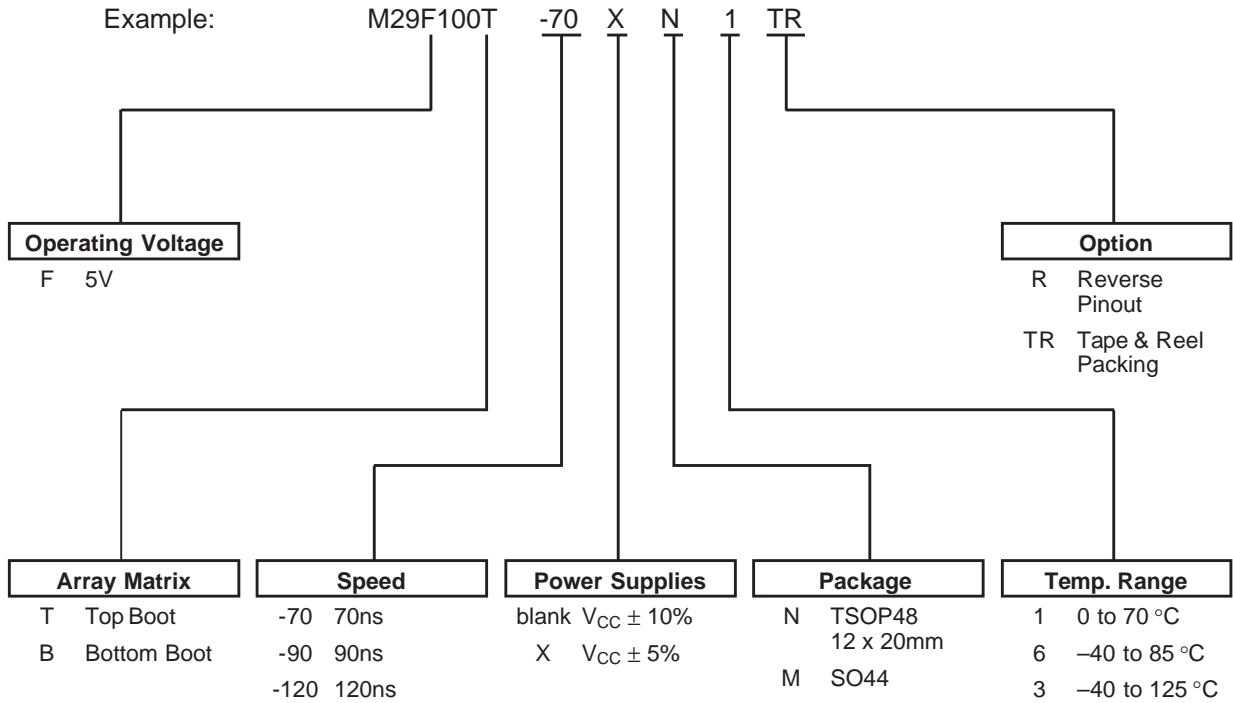


Warning: NC = Not Connected.

Signal Names

A0-A15	Address Inputs
DQ0-DQ7	Data Input/Outputs, Command Inputs
DQ8-DQ14	Data Input/Outputs
DQ15A-1	Data Input/Output or Address Input
E-bar	Chip Enable
G-bar	Output Enable
W-bar	Write Enable
RP-bar	Reset / Block Temporary Unprotect
RB-bar	Ready/Busy Output
BYTE-bar	Byte/Word Organisation
V _{CC}	Supply Voltage
V _{SS}	Ground

ORDERING INFORMATION SCHEME



Devices are shipped from the factory with the memory content erased (to FFh).

For a list of available options (Speed, Package, etc...) or for further information on any aspect of this device, please contact the STMicroelectronics Sales Office nearest to you.